

General Description

The WSD30140DN56 is the highest performance trench N-Ch MOSFET with extreme high celldensity ,which provide excellent R_{DSON} and gate charge for most of the synchronous buck converter applications .

The WSD30140DN56 meet the RoHS and Green Product requirement , 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

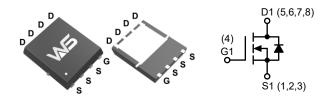
Product Summery

BV _{DSS}	R _{DSON}	I _D
30V	1.7mΩ	85A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter
- Networking DC-DC Power System
- Power Tool Application

DFN5X6-8L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units	
V_{DS}	Drain-Source Voltage	30	V	
V_{GS}	Gate-Source Voltage	±20	V	
I _D @T _C =25℃	Continuous Drain Current, V _{GS} @ 10V ^{1,7}	85	Α	
I _D @T _C =70°C	Continuous Drain Current, V _{GS} @ 10V ^{1,7}	65	Α	
I _{DM}	Pulsed Drain Current ²	300	Α	
P _D @T _C =25℃	Total Power	50	W	
T _{STG}	Storage Temperature Range	-55 to 150	$^{\circ}$	
TJ	Operating Junction Temperature Range -55 to 150			

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
$R_{ heta JA}$	Thermal Resistance Junction-Ambient 1		55	°C/W
$R_{ heta JC}$	Thermal Resistance Junction-Case ¹		1.5	°C/W



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	30			V
$\triangle BV_{DSS}/\triangle T_{J}$	BV _{DSS} Temperature Coefficient	Reference to 25 $^{\circ}\mathrm{C}$, I _D =1mA		0.02		V/°C
-	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =20A		1.7	2.4	mΩ
R _{DS(ON)}		V _{GS} =4.5V , I _D =15A		2.5	3.3	
V _{GS(th)}	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250uA$	1.2	1.7	2.5	V
	Drain-Source Leakage Current	V_{DS} =24V , V_{GS} =0V , T_J =25 $^{\circ}$ C			1	- uA
I _{DSS}		V_{DS} =24V , V_{GS} =0V , T_J =55 $^{\circ}$ C			5	
I _{GSS}	Gate-Source Leakage Current	V_{GS} = $\pm 20V$, V_{DS} = $0V$			±100	nA
gfs	Forward Transconductance	V _{DS} =5V , I _D =20A		90		S
Qg	Total Gate Charge (4.5V)	V _{DS} =15V , V _{GS} =4.5V , I _D =20A		26		
Q _{gs}	Gate-Source Charge			9.5		nC
Q _{gd}	Gate-Drain Charge			11.4		
T _{d(on)}	Turn-On Delay Time			6		
Tr	Rise Time	V_{DD} =15V , V_{GEN} =10V , R_{G} =3 Ω , RL=0.75 Ω .		11		no
T _{d(off)}	Turn-Off Delay Time			10		ns
	Fall Time			38.5		
Ciss	Input Capacitance			3000		
C _{oss}	Output Capacitance	V _{DS} =15V , V _{GS} =0V , f=1MHz		1280		pF
C _{rss}	Reverse Transfer Capacitance			160		

Diode Characteristics

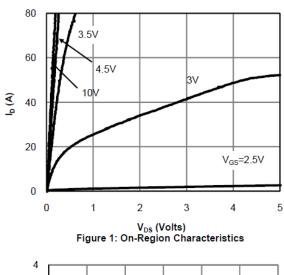
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
I _S	Continuous Source Current ^{1,6}	V _G =V _D =0V , Force Current			85	Α
V_{SD}	Diode Forward Voltage ²	V_{GS} =0V , I_{S} =A , T_{J} =25 $^{\circ}$ C			1.2	V

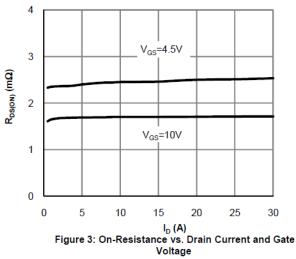
A: The value of RθJA is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with TA=25°C. The value in any given application depends on the user's specific board design.

- B: Repetitive rating, pulse width limited by junction temperature.
- C: The current rating is based on the t≤ 10s junction to ambient thermal resistance rating.

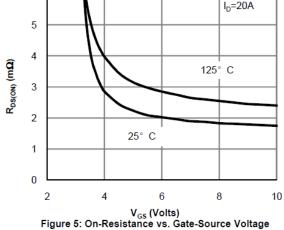


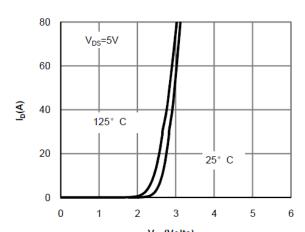
Typical Characteristics











V_{GS}(Volts) Figure 2: Transfer Characteristics

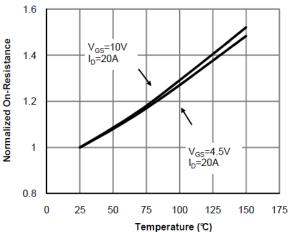
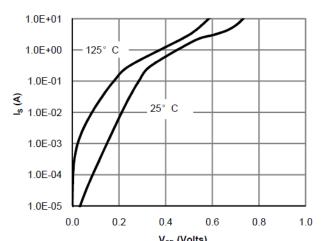
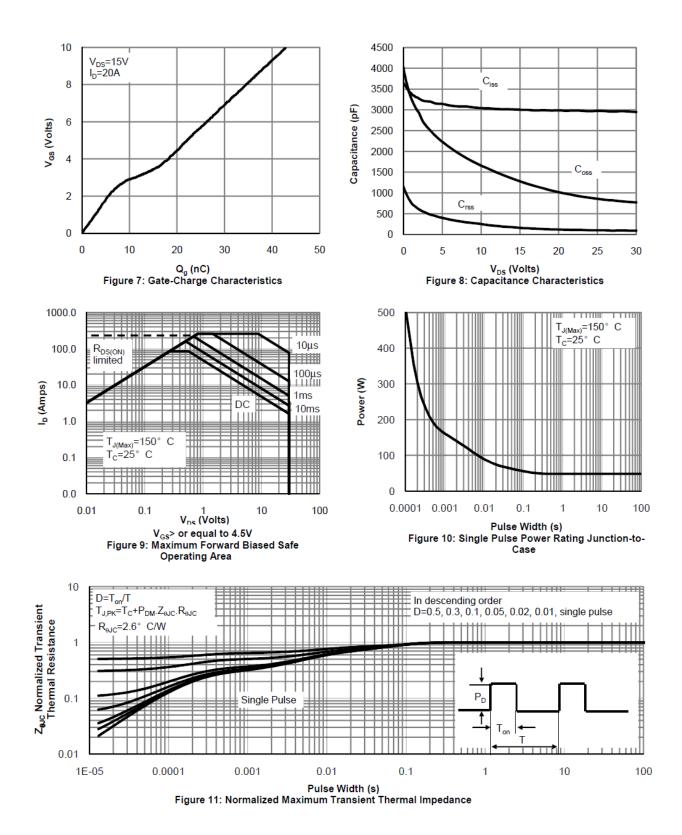


Figure 4: On-Resistance vs. Junction Temperature



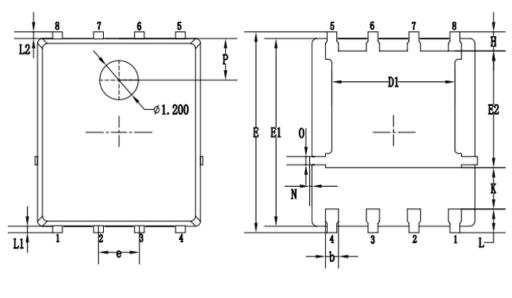
V_{SD} (Volts) Figure 6: Body-Diode Characteristics

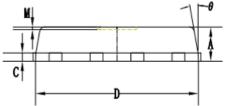






Packaging information





CVMDOLO		MILLIMETERS			
SYMBOLS	MIN.	NOM.	MAX.		
Α	0.90	1.05	1.20		
b	0.35	0.40	0.50		
С	0.20	0.25	0.35		
D	4.90	5.05	5.20		
D1	3.72	3.82	3.92		
E	6.00	6.15	6.30		
E1	5.60	5.75	5.90		
E2	3.47	3.57	3.67		
е		1.27 BSC.			
Н	0.48	0.58 0			
K	1.17	1.27	1.37		
L	0.64	0.74	0.84		
L1/L2		0.20 REF.			
θ	8°	10°	12°		
М		0.08 REF.			
N	0	-	0.15		
0		0.25 REF.			
Р		1.28 REF.			



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